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EUROPEAN PATENT APPLICATION

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⑬ Composite comprising a silicon substrate and layered superconducting thin films.

⑭ A composite comprising a silicon substrate (1) and a plurality of layers of a first oxide superconductor layer (3), a dielectric material layer (4), a second oxide superconductor layer (5), a second dielectric material layer (6) and a third oxide superconductor layer (7) deposited directly or through a buffer layer (2) in this order on the silicon substrate.

The composite is used for fabricating superconducting devices such as Josephson element, SQUID and microwave devices.

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DOCUMENTS CONSIDERED TO BE RELEVANT			EP 91401967.4
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int. CL.5)
X	<u>DE - A1 - 3 812 662</u> (HITACHI) * Column 8, lines 35-67; column 13, lines 21-33; fig. 8 *	1, 6-9	H 01 L 23/485 H 01 L 39/00
X;Y	<u>DE - A1 - 3 810 494</u> (HITACHI) * Column 12, lines 29-64; column 6, lines 29-44; fig. 13 *	1, 4-6, 10, 14; 2, 3, 11-13, 15, 16	
Y	<u>EP - A1 - 0 301 646</u> (PHILIPS) * Column 1, line 13 - column 2, line 53 *	2, 3, 11-13	
Y	<u>EP - A2 - 0 307 246</u> (SEMICONDUCTOR) * Embodiments *	15	
Y	APPLIED PHYSICS LETTERS, vol. 51, No. 3, July 20, 1987 R.H. KOCH et al. "Quantum interference devices made from superconducting oxide thin films" pages 200-202 * Abstract *	16	TECHNICAL FIELDS SEARCHED (Int. CL.5) H 01 L H 01 B 12/00
The present search report has been drawn up for all claims			
Place of search VIENNA	Date of completion of the search 17-10-1991	Examiner KUTZELNIGG	
CATEGORY OF CITED DOCUMENTS		T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons & : member of the same patent family, corresponding document	
X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document			